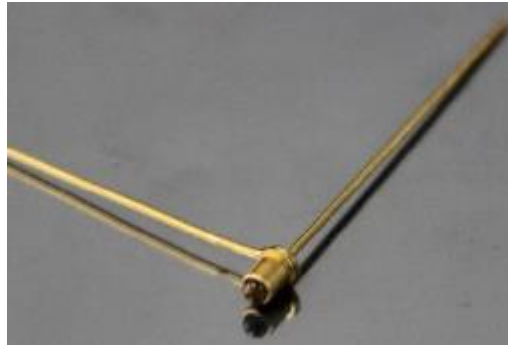


# GaN Broad Band UV Photodiode

UV0.1TB-2



## Description

UV0.1TB-2 is broad band GaN based UV photodiode. It is optimized for Ultra-violet range 210~370 nm, It can be easily selected with integral filters. It is packaged in electrically isolated and hermetically sealed TO Mini-Metal can with quartz window.

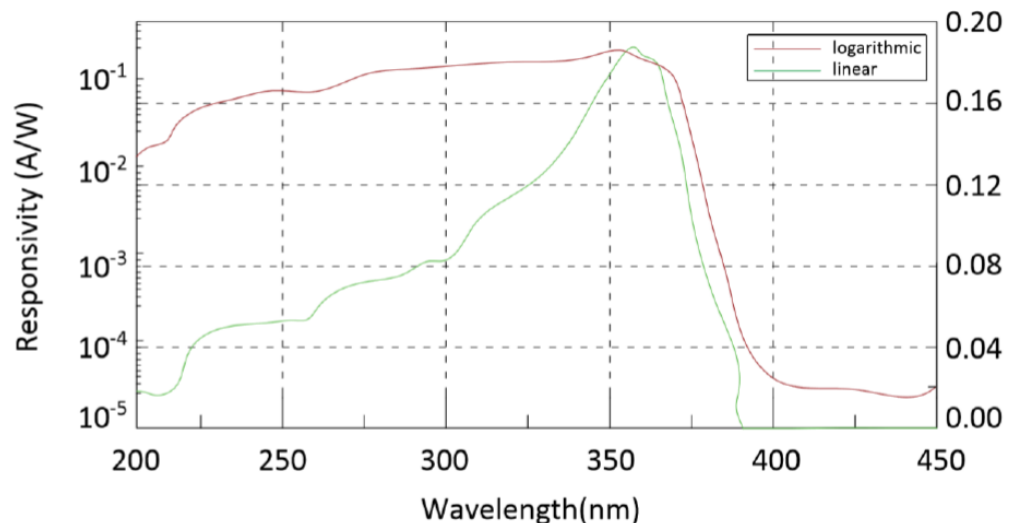
## Features

\*High reliability in demanding environments

## Applications

- \* Sunlight exposure meter
- \* Water purification facilities
- \* UV power meter

## Spectral Response



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Components

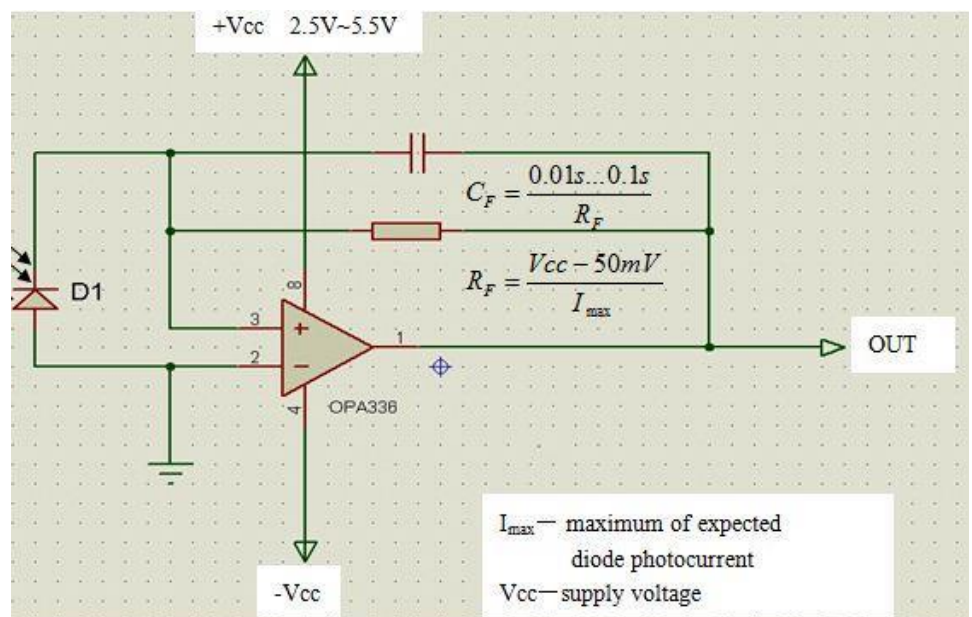


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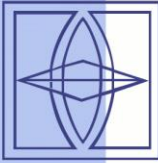
## Electro-Optical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operation temperature range	Topt	-25		+85	°C
Storage temperature range	Tsto	-40		+85	°C
Soldering temperature (3s)	Tsol		260		°C
Reverse voltage	Vr		-10		V
Chip size (active area)	A		0.1		mm <sup>2</sup>
Dark current (Vr=-5V)	Id			1	nA
Temperature coefficient	Tc		-0.02		%/°C
Capacitance (Vr=0V, f=1MHz)	Cj		3.4		pF
Wavelength of peak responsivity	$\lambda_p$		355		nm
Peak responsivity (@355nm)	Rmax		0.15		A/W
Spectral response range (R=0.1*Rmax)	S <sub>R</sub>	210		375	nm
UV-Visible rejection ratio(Rmax/R400nm)	-	10 <sup>4</sup>			-

## Typical Application Circuit



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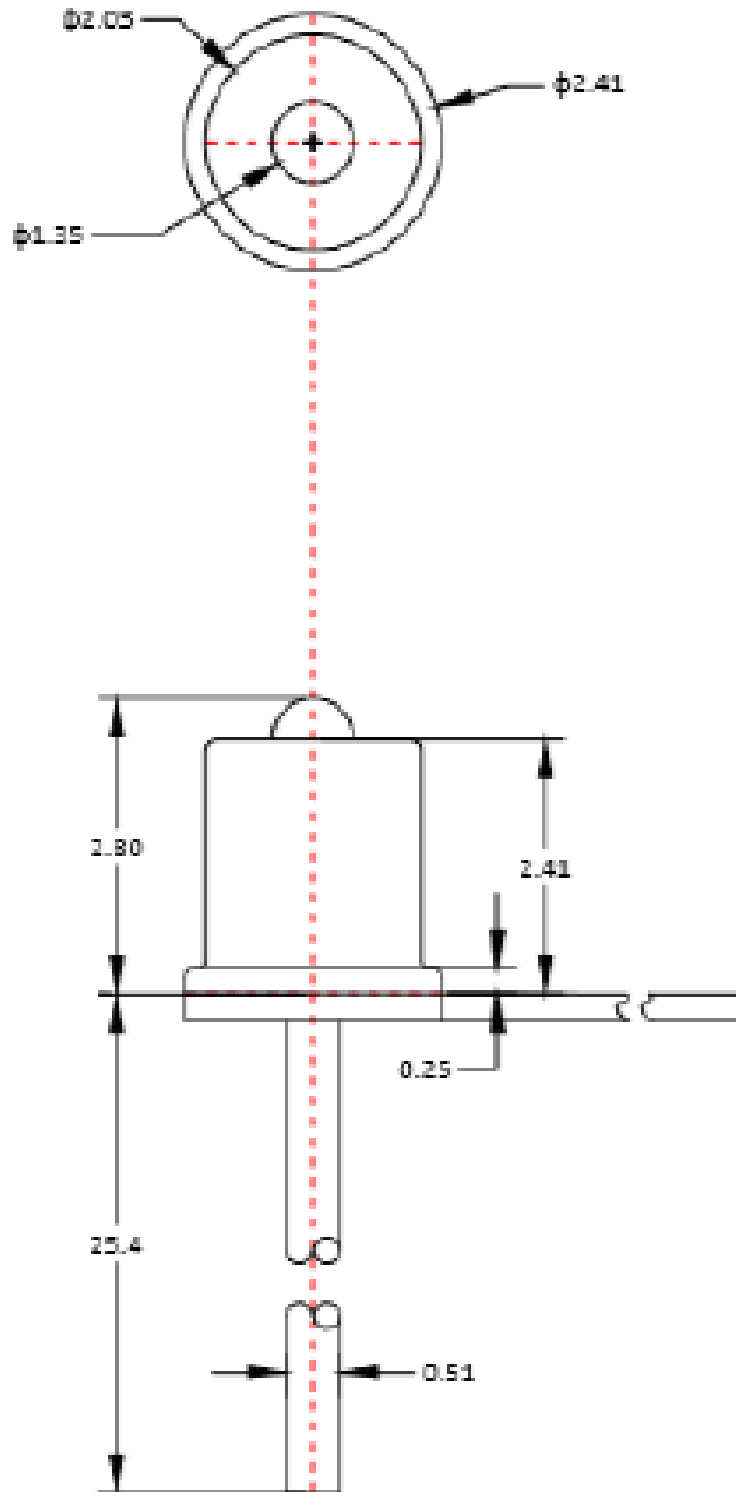


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## Package Drawing



All Dimensions in „mm“